

Michael V Yakushev

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

147
papers

1,101
citations

19
h-index

25
g-index

152
ext. papers

1,216
ext. citations

1.6
avg, IF

3.75
L-index

#	Paper	IF	Citations
147	Diffusion Limitation of Dark Current in the nBn Structures Based on the MBE HgCdTe. <i>Journal of Communications Technology and Electronics</i> , 2022 , 67, 308-312	0.5	0
146	Mapping the Energetics of Defect States in CuZnSnS films and the Impact of Sb Doping.. <i>ACS Applied Energy Materials</i> , 2022 , 5, 3933-3940	6.1	0
145	Photoluminescence, stimulated and laser emission in CuInSe ₂ crystals. <i>Applied Physics Letters</i> , 2021 , 119, 212103	3.4	0
144	Radiative Recombination at Ion-Induced Defects in Cu(In,Ga)Se ₂ Alloy Thin Films. <i>Semiconductors</i> , 2021 , 55, 168-174	0.7	1
143	Structural Characteristics and Photoluminescence of Thin Films of Cu(In _{1-x} Ga _x)(S _y Se _{1-y}) ₂ Solid Solutions. <i>Journal of Applied Spectroscopy</i> , 2021 , 88, 27-32	0.7	1
142	Ellipsometric In Situ Methods of Temperature Control in the Technology of Growing MBE MCT Layers. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2021 , 57, 476-484	0.6	
141	Admittance of MIS Structures Based on nBn Systems of Epitaxial HgCdTe for Detection in the 3B μ m Spectral Range. <i>Technical Physics Letters</i> , 2021 , 47, 629-632	0.7	
140	The g-factor of CuGaSe ₂ studied by circularly polarised magneto-reflectance. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 17LT02	3	
139	Possibilities of Characterizing the Crystal Parameters of Cd _x Hg _{1-x} Te Structures on GaAs Substrates by the Method of Generation of the Probe-Radiation Second Harmonic in Reflection Geometry. <i>Physics of the Solid State</i> , 2020 , 62, 252-259	0.8	3
138	HgCdTe-Based 640 \times 12 Matrix Midwave Infrared Photodetector. <i>Journal of Communications Technology and Electronics</i> , 2020 , 65, 316-320	0.5	1
137	Parametric Model of the Optical Constant Spectra of Hg _{1-x} Cd _x Te and Determination of the Compound Composition. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2020 , 128, 1948-1953	0.7	2
136	The Effect of the Growth Temperature on the Passivating Properties of the Al ₂ O ₃ Films Formed by Atomic Layer Deposition on the CdHgTe Surface. <i>Technical Physics Letters</i> , 2020 , 46, 741-744	0.7	2
135	Molecular Beam Epitaxy of CdHgTe: Current State and Horizons. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2020 , 56, 456-469	0.6	2
134	Optical and Structural Properties of HgCdTe Solid Solutions with a High CdTe Content. <i>Semiconductors</i> , 2020 , 54, 1561-1566	0.7	1
133	A Magneto-Reflectivity Study of CuInTe ₂ Single Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900464	1.3	
132	Spontaneous and Stimulated Emission in Thin Films of Cu(In _{1-x} Ga _x)(S _y Se _{1-y}) ₂ Solid Solutions in the μ m Composition of Solar Cells. <i>Semiconductors</i> , 2020 , 54, 1247-1253	0.7	
131	A Megapixel Matrix Photodetector of the Middle Infrared Range. <i>Journal of Communications Technology and Electronics</i> , 2019 , 64, 1011-1015	0.5	2

130	Capacitive Properties of Metal-Insulator-Semiconductor Systems Based on an HgCdTe nBn Structure Grown by Molecular Beam Epitaxy. <i>Journal of Communications Technology and Electronics</i> , 2019 , 64, 289-293	0.5	5
129	A PL and PLE Study of High Cu Content Cu ₂ ZnSnSe ₄ Films on Mo/Glass and Solar Cells. <i>Physics of the Solid State</i> , 2019 , 61, 908-917	0.8	1
128	Excitons in PL Spectra of Cu(In,Ga)Se ₂ Single Crystals. <i>Physics of the Solid State</i> , 2019 , 61, 918-924	0.8	1
127	Ellipsometric Method for Measuring the CdTe Buffer-Layer Temperature in the Molecular-Beam Epitaxy of CdHgTe. <i>Semiconductors</i> , 2019 , 53, 132-137	0.7	3
126	The band structure of CuInTe ₂ studied by optical reflectivity. <i>Applied Physics Letters</i> , 2019 , 114, 062103	3.4	4
125	An Optical Study of Disorder in Cadmium Mercury Telluride Solid Solutions. <i>Technical Physics Letters</i> , 2019 , 45, 553-556	0.7	0
124	Photodetectors with 384 × 88 Matrix Elements for the Infrared Range of 8–10 Microns. <i>Journal of Communications Technology and Electronics</i> , 2019 , 64, 1024-1029	0.5	3
123	Express Characterization of Crystalline Perfection of Cd _x Hg _{1-x} Te Structures by Reflection Second Harmonic Generation of Probing Radiation. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2019 , 55, 447-454	0.6	2
122	A luminescence study of Cu ₂ ZnSnSe ₄ /Mo/glass films and solar cells with near stoichiometric copper content. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 055502	3	3
121	Effects of selenisation temperature on photoluminescence and photoluminescence excitation spectra of ZnO/CdS/Cu ₂ ZnSnSe ₄ /Mo/glass. <i>Thin Solid Films</i> , 2019 , 672, 146-151	2.2	1
120	A Magneto-Reflectivity Study of CuGaSe ₂ Single Crystals. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1800374	2.5	2
119	Stimulated Emission and Optical Properties of Solid Solutions of Cu(In,Ga)Se ₂ Direct Band Gap Semiconductors. <i>Journal of Applied Spectroscopy</i> , 2018 , 85, 267-273	0.7	
118	The Effect of Copper on the Electronic Structure and Effective Masses of CuIn ₅ Se ₈ Single Crystals Revealed by Angle-Resolved Photoemission Spectroscopy. <i>Physics of Metals and Metallography</i> , 2018 , 119, 430-435	1.2	
117	Investigation of the Strongly Correlated Two-Hole State of Copper in Resonant Photoemission States of Chalcogenide Materials for Photovoltaics. <i>Physics of Metals and Metallography</i> , 2018 , 119, 520-522	1.2	1
116	Impact of the Graded-Gap Layer on the Admittance of MIS Structures Based on MBE-Grown n-Hg _{1-x} Cd _x Te (x = 0.22–0.23) with the Al ₂ O ₃ Insulator. <i>Journal of Communications Technology and Electronics</i> , 2018 , 63, 281-284	0.5	
115	Advanced Design of Scanning Infrared Focal Plane Arrays. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2018 , 54, 569-575	0.6	0
114	Effects of Ar ⁺ etching of Cu ₂ ZnSnSe ₄ thin films: An x-ray photoelectron spectroscopy and photoluminescence study. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 061208	1.3	4
113	Luminescence and Stimulated Emission of Polycrystalline Cu(In,Ga)Se ₂ Films Deposited by Magnetron-Assisted Sputtering. <i>Semiconductors</i> , 2018 , 52, 1238-1243	0.7	

112	Influence of the growth method on the photoluminescence spectra and electronic properties of CuInS ₂ single crystals. <i>Journal of Luminescence</i> , 2017 , 186, 123-126	3.8	4
111	Influence of the copper content on the optical properties of CZTSe thin films. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 168, 69-77	6.4	29
110	Defect levels and hyperfine constants of hydrogen in beryllium oxide from hybrid-functional calculations and muonium spectroscopy. <i>Philosophical Magazine</i> , 2017 , 97, 2108-2128	1.6	7
109	Spectroscopic and electrical signatures of acceptor states in solution processed Cu ₂ ZnSn(S,Se) ₄ solar cells. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 12720-12727	7.1	15
108	Methodological and instrumental problems in high-precision in situ ellipsometry diagnostics of the mercury cadmium telluride layer composition in molecular beam epitaxy. <i>Instruments and Experimental Techniques</i> , 2016 , 59, 857-864	0.5	4
107	Defects in mercury-cadmium telluride heteroepitaxial structures grown by molecular-beam epitaxy on silicon substrates. <i>Semiconductors</i> , 2016 , 50, 208-211	0.7	2
106	A photoluminescence study of CuInSe ₂ single crystals ion implanted with 5 keV hydrogen. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 105108	3	8
105	Stimulated emission and lasing in Cu(In,Ga)Se ₂ thin films. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 095106	3	6
104	CdHgTe heterostructures for new-generation IR photodetectors operating at elevated temperatures. <i>Semiconductors</i> , 2016 , 50, 1626-1629	0.7	4
103	Characterization of vacancy defects in Cu(In,Ga)Se ₂ by positron annihilation spectroscopy. <i>AIP Advances</i> , 2016 , 6, 125031	1.5	4
102	RBS-channeling study of radiation damage in Ar ⁺ implanted CuInSe ₂ crystals. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 051203	2.9	1
101	Strong interband Faraday rotation in 3D topological insulator Bi ₂ Se ₃ . <i>Scientific Reports</i> , 2016 , 6, 19087	4.9	5
100	Optical spectroscopy studies of Cu ₂ ZnSnSe ₄ thin films. <i>Thin Solid Films</i> , 2015 , 582, 154-157	2.2	12
99	A photoluminescence study of excitonic grade CuInSe ₂ single crystals irradiated with 6 MeV electrons. <i>Journal of Applied Physics</i> , 2015 , 118, 155703	2.5	8
98	Radiative recombination in Cu ₂ ZnSnSe ₄ thin films with Cu deficiency and Zn excess. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 475109	3	14
97	Photoluminescence of CdHgTe solid solutions subjected to low-energy ion treatment. <i>Semiconductors</i> , 2014 , 48, 195-198	0.7	4
96	Electronic and structural characterisation of Cu ₃ BiS ₃ thin films for the absorber layer of sustainable photovoltaics. <i>Thin Solid Films</i> , 2014 , 562, 195-199	2.2	31
95	Influence of Chemical Composition Heterogeneity on the Spectral Position of the Fundamental Absorption Edge of Cu(In, Ga)Se ₂ Solid Solutions. <i>Journal of Applied Spectroscopy</i> , 2014 , 81, 404-410	0.7	1

94	Dislocations in CdTe heteroepitaxial structures on GaAs(301) and Si(301) substrates. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2014 , 50, 234-240	0.6	6
93	Effect of mechanical compression on Cu(In,Ga)Se ₂ films: micro-structural and photoluminescence analysis. <i>RSC Advances</i> , 2014 , 4, 5141	3.7	2
92	CdHgTe heterostructures on large-area Si(310) substrates for infrared photodetector arrays of the short-wavelength spectral range. <i>Semiconductors</i> , 2014 , 48, 767-771	0.7	5
91	Investigation of the Structural, Optical and Electrical Properties of Cu ₃ BiS ₃ Semiconducting Thin Films. <i>Energy Procedia</i> , 2014 , 60, 166-172	2.3	7
90	Landau levels of the C-exciton in CuInSe ₂ studied by magneto-transmission. <i>Applied Physics Letters</i> , 2014 , 105, 142103	3.4	3
89	Dual-wavelength stimulated emission from a double-layer Cd _x Hg _{1-x} Te structure at wavelengths of 2 and 3 μ m. <i>JETP Letters</i> , 2013 , 97, 358-361	1.2	1
88	High-temperature photoluminescence of CdHgTe solid solutions grown by molecular-beam epitaxy. <i>Technical Physics</i> , 2013 , 58, 1536-1539	0.5	4
87	Ion channeling in CuInSe ₂ single crystals. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2013 , 299, 24-28	1.2	1
86	Resonant photoemission spectroscopy of Cu(InGa)Se ₂ materials for solar cells. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2013 , 77, 1123-1126	0.4	8
85	Photoelectric characteristics of diodes in prototype photosensitive pixels for a monolithic array infrared photodetector. <i>Semiconductors</i> , 2012 , 46, 535-540	0.7	2
84	Anisotropy of effective masses in CuInSe ₂ . <i>Applied Physics Letters</i> , 2012 , 101, 262101	3.4	13
83	Electrical and optical properties of CdHgTe films grown by molecular-beam epitaxy on silicon substrates. <i>Semiconductors</i> , 2012 , 46, 1341-1345	0.7	4
82	Excitation power and temperature dependence of excitons in CuInSe ₂ . <i>Journal of Applied Physics</i> , 2012 , 111, 093507	2.5	29
81	A photoelectron spectroscopy study of the electronic structure evolution in CuInSe ₂ -related compounds at changing copper content. <i>Applied Physics Letters</i> , 2012 , 101, 111607	3.4	11
80	Excited States of the A and B Free Excitons in CuInSe ₂ . <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 05FC03	1.4	1
79	Optical properties of high quality Cu ₂ ZnSnSe ₄ thin films. <i>Applied Physics Letters</i> , 2011 , 99, 062104	3.4	77
78	Incorporation of hydrogen in CuInSe ₂ : Improvements of the structure. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011 , 29, 051201	2.9	6
77	Fabrication and characterisation of Cu(In,Ga)Se ₂ solar cells on polyimide. <i>Thin Solid Films</i> , 2011 , 519, 7264-7267	2.2	16

76	Infrared focal plane assemblies based on HgCdTe/Si(310) heterostructure. <i>Technical Physics Letters</i> , 2011 , 37, 148-150	0.7	1
75	HgCdTe heterostructures on Si (310) substrates for midinfrared focal plane arrays. <i>Semiconductors</i> , 2011 , 45, 385-391	0.7	30
74	Photoluminescence of Hg _{1-x} Cd _x Te based heterostructures grown by molecular-beam epitaxy. <i>Semiconductors</i> , 2011 , 45, 872-879	0.7	19
73	Defects in the crystal structure of Cd _x Hg _{1-x} Te layers grown on the Si (310) substrates. <i>Semiconductors</i> , 2011 , 45, 926-934	0.7	9
72	Excited States of the A and B Free Excitons in CuInSe ₂ . <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 05FC03	1.4	1
71	Diamagnetic shift of the A free exciton in CuGaSe ₂ single crystals. <i>Applied Physics Letters</i> , 2010 , 97, 162104	0.7	20
70	Excited states of the free excitons in CuInSe ₂ single crystals. <i>Applied Physics Letters</i> , 2010 , 97, 152110	3.4	36
69	Monitoring the composition of the Cd _{1-x} Zn _x Te heteroepitaxial layers by spectroscopic ellipsometry. <i>Semiconductors</i> , 2010 , 44, 59-65	0.7	
68	Surface micromorphology of CdTe(310) layers grown by molecular beam epitaxy. <i>Journal of Surface Investigation</i> , 2010 , 4, 64-70	0.5	4
67	Structural and optical properties of thin films of Cu(In,Ga)Se ₂ semiconductor compounds. <i>Journal of Applied Spectroscopy</i> , 2010 , 77, 371-377	0.7	27
66	Structural and optical properties of CdS/Cu(In,Ga)Se ₂ heterostructures irradiated by high-energy electrons*. <i>Journal of Applied Spectroscopy</i> , 2010 , 77, 668-674	0.7	3
65	Diamagnetic shifts of free excitons in CuInS ₂ in magnetic fields. <i>Applied Physics Letters</i> , 2009 , 94, 042109	3.4	9
64	Photoluminescence of CuInS ₂ single crystals grown by traveling heater and chemical vapor transport methods. <i>Journal of Applied Spectroscopy</i> , 2009 , 76, 215-219	0.7	1
63	Effects of magnetic fields on free excitons in CuInSe ₂ . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 1086-1088		5
62	Temperature dependence of excitonic emission in CuInSe ₂ . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 1082-1085		8
61	Effect of orientation of the substrate on the conditions of growth of HgTe films by molecular beam epitaxy. <i>Inorganic Materials</i> , 2009 , 45, 13-18	0.9	3
60	HgCdTe heterostructures on Si(310) substrates for infrared photodetectors. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2009 , 45, 301-307	0.6	
59	Interaction of cadmium vapor with the surface of Cd _x Hg _{1-x} Te layers during molecular beam epitaxial growth on GaAs substrates. <i>Inorganic Materials</i> , 2008 , 44, 366-370	0.9	1

58	Excited states of the A free exciton in CuInS ₂ . <i>Applied Physics Letters</i> , 2008 , 92, 111908	3.4	26
57	Surface morphology of a Si(310) substrate used for molecular beam epitaxy of CdHgTe: II. Si(310) surface annealed in As ₄ vapors. <i>Journal of Surface Investigation</i> , 2008 , 2, 433-439	0.5	
56	Optical spectroscopy of free excitons in a CuInS ₂ chalcopyrite semiconductor compound. <i>Semiconductors</i> , 2008 , 42, 29-33	0.7	2
55	Dependence of the electrical parameters of MBE-grown Cd x Hg _{1-x} Te films on the level of doping with indium. <i>Semiconductors</i> , 2008 , 42, 648-650	0.7	8
54	Magnetic field effect on free and bound excitons in chalcopyrite CuInS ₂ . <i>Journal of Applied Spectroscopy</i> , 2007 , 74, 415-420	0.7	2
53	Energy of excitons in CuInS ₂ single crystals. <i>Applied Physics Letters</i> , 2006 , 88, 011922	3.4	33
52	First-principles study of deformation behavior and structural defects in CuInSe ₂ and Cu(In,Ga)Se ₂ . <i>Physical Review B</i> , 2006 , 73,	3.3	22
51	Excitons in high-quality CuInS ₂ single crystals. <i>Thin Solid Films</i> , 2006 , 511-512, 130-134	2.2	12
50	Effect of γ radiation on photosensitivity of ZnO/CuIn ₃ Se ₅ heterojunctions. <i>Semiconductors</i> , 2006 , 40, 64-66	0.7	3
49	Defect formation in thin films of the semiconductor compound Cu(In,Ga)Se ₂ when bombarded by protons. <i>Journal of Applied Spectroscopy</i> , 2006 , 73, 928-931	0.7	3
48	Observation of antiphase domains in Cd _x Hg _{1-x} Te films on silicon by the phase contrast method in atomic force microscopy. <i>JETP Letters</i> , 2005 , 82, 292-296	1.2	1
47	Photosensitivity of photocells based on ZnO/CdS/Cu(In, Ga)Se ₂ heterostructures and exposed to γ radiation. <i>Semiconductors</i> , 2005 , 39, 1406	0.7	5
46	Radiation-induced defects in thin Cu(In,Ga)Se ₂ films on exposure to high-energy electron irradiation. <i>Journal of Applied Spectroscopy</i> , 2005 , 72, 883-886	0.7	3
45	Low-temperature photoluminescence in AgGaSe ₂ single crystals. <i>Technical Physics</i> , 2004 , 49, 335-337	0.5	5
44	Fabrication and photosensitivity of heterojunctions based on CuIn ₃ Se ₅ crystals. <i>Semiconductors</i> , 2004 , 38, 1192-1197	0.7	2
43	XPS and XPD investigation of (112) CuInSe ₂ and Cu(In,Ga)Se ₂ surfaces. <i>Thin Solid Films</i> , 2004 , 451-452, 137-140	2.2	4
42	Effects of deviation from stoichiometry on excitons in CuInSe ₂ single crystals. <i>Thin Solid Films</i> , 2003 , 431-432, 190-192	2.2	4
41	Diffusion effects at the Au/p-CuInSe ₂ contact studied by XPS. <i>Crystal Research and Technology</i> , 2003 , 38, 676-683	1.3	5

40	Comparative study of Er-implanted Si, ZnAs ₂ and CuInSe ₂ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 105, 175-178	3.1	3
39	Optical properties and band gap energy of CuInSe ₂ thin films prepared by two-stage selenization process. <i>Journal of Physics and Chemistry of Solids</i> , 2003 , 64, 2005-2009	3.9	19
38	Magneto-photoluminescence study of radiative recombination in CuInSe ₂ single crystals. <i>Journal of Physics and Chemistry of Solids</i> , 2003 , 64, 2011-2016	3.9	10
37	Spontaneous formation of the periodic composition-modulated nanostructure in Cd _x Hg _{1-x} Te films. <i>Semiconductors</i> , 2003 , 37, 1331-1335	0.7	4
36	Energy of free excitons in CuInSe ₂ single crystals. <i>Applied Physics Letters</i> , 2003 , 82, 3233-3235	3.4	7
35	The effect of a surface layer on determination of the dielectric functions of ZnTe films by the ellipsometric technique. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2002 , 92, 780-783	0.7	
34	Photosensitivity of structures based on I-III-V ternary compounds containing ordered vacancies. <i>Semiconductors</i> , 2002 , 36, 1132-1135	0.7	3
33	Photoelectric Properties of the In/CuIn ₃ Se ₅ and In/CuGa ₃ Se ₅ Structures. <i>Journal of Applied Spectroscopy</i> , 2002 , 69, 602-605	0.7	
32	Effects of D ⁺ implantation of CIGS thin films through a CdS layer. <i>Thin Solid Films</i> , 2001 , 387, 201-204	2.2	8
31	In situ XPS investigations of ion beam hydrogenation of CuInSe ₂ . <i>Thin Solid Films</i> , 2001 , 387, 185-188	2.2	4
30	Molecular-beam epitaxy of mercury-cadmium-telluride solid solutions on alternative substrates. <i>Semiconductors</i> , 2001 , 35, 1045-1053	0.7	47
29	Optical spectroscopy of excitonic states in CuInSe ₂ . <i>Semiconductors</i> , 2000 , 34, 534-537	0.7	9
28	Molecular static model of CuInSe ₂ crystal: Energy properties of some structural defects. <i>Physics of the Solid State</i> , 2000 , 42, 1643-1647	0.8	
27	Photoluminescence spectra of the AgGaTe ₂ single crystals doped with hydrogen. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2000 , 88, 377-379	0.7	4
26	A Photoluminescence Study of Hydrogen-Implanted Cu(InGa)Se ₂ Thin Films. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 320	1.4	5
25	Optical Properties of Excitonic-Grade CuInSe ₂ Single Crystals. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 92	1.4	3
24	Photoluminescence Studies of Low Energy Hydrogen-Implanted AgGaTe ₂ Single Crystals. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 114	1.4	
23	Optical properties of high-quality CuInSe ₂ single crystals. <i>Applied Physics Letters</i> , 2000 , 77, 2542-2544	3.4	29

22	Low energy ion beam etching of CuInSe ₂ surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 19-25	2.9	24
21	Modeling hydrogen in CuInSe ₂ and CuInS ₂ solar cell materials using implanted muons. <i>Physical Review B</i> , 1999 , 59, 1912-1916	3.3	20
20	A rutherford backscattering spectrometry study of Zn implanted BeO single crystals. <i>Radiation Effects and Defects in Solids</i> , 1999 , 150, 157-160	0.9	3
19	On the redistribution of 10keV hydrogen in CuInSe ₂ . <i>Radiation Effects and Defects in Solids</i> , 1998 , 145, 85-105	0.9	8
18	Hydrogen Diffusion in Chalcopyrite Solar Cell Materials. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 513, 177		4
17	A Raman Scattering, Ion Channelling and Photoluminescence Study of Argon Ion Radiation Damage in Cu(Ga,In)Se ₂ - Dose Dependence and Dose Rate Effects. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 540, 85		
16	Modification of the CuInSe ₂ Crystal Surface during Polishing and Annealing. <i>Crystal Research and Technology</i> , 1997 , 32, 155-161	1.3	
15	Optical Investigation of Defects in p-type CuInSe ₂ Single Crystals. <i>Crystal Research and Technology</i> , 1996 , 31, 63-74	1.3	3
14	XPS Analysis of Bridgman-grown CuInTe ₂ and of its Native Oxide. <i>Crystal Research and Technology</i> , 1996 , 31, 75-85	1.3	12
13	A Rutherford backscattering-channelling and Raman study of CuInSe ₂ single crystal surfaces. <i>Journal of Materials Science: Materials in Electronics</i> , 1996 , 7, 155	2.1	14
12	The effects of ion implantation on the microstructure of CuInSe ₂ single crystals. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1996 , 73, 1131-1145		9
11	Photoacoustic spectroscopy use in the analysis of ion-implanted CuInSe ₂ single crystals. <i>Review of Scientific Instruments</i> , 1995 , 66, 4095-4101	1.7	17
10	Ion channeling study of defects in CuInTe ₂ single crystals. <i>Crystal Research and Technology</i> , 1995 , 30, 121-128	1.3	2
9	Photoacoustic Spectroscopy of Defect States in Etched and Air-annealed CuInSe ₂ Single Crystals. <i>Crystal Research and Technology</i> , 1995 , 30, 517-530	1.3	5
8	Influence of proton implantation on the properties of CuInSe ₂ single crystals (I). Ion channeling study of lattice damage. <i>Crystal Research and Technology</i> , 1994 , 29, 125-132	1.3	16
7	Influence of proton implantation on the properties of CuInSe ₂ single crystals (II). <i>Crystal Research and Technology</i> , 1994 , 29, 417-426	1.3	20
6	Effect of plasma hydrogenation on the defect properties of CuInSe ₂ single crystals. <i>Crystal Research and Technology</i> , 1994 , 29, 427-437	1.3	16
5	Comparative optical absorption and photoreflectance study of n-type CuInSe ₂ single crystals. <i>Crystal Research and Technology</i> , 1994 , 29, 719-726	1.3	9

4	Electrical Properties of CuInSe ₂ Single Crystals Implanted with Xenon. <i>Crystal Research and Technology</i> , 1993 , 28, 267-272	1.3	10
3	Studies of the Effects of Ion-Implantation and Electron Beam Irradiation on CuInSe ₂ Single Crystals. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 262, 1097		7
2	Changes in the opto-electronic properties of CuInSe ₂ following ion implantation. <i>Journal of Electronic Materials</i> , 1991 , 20, 659-663	1.9	25
1	Diode n-p CuInSe ₂ Structures Fabricated by Oxygen Implantation. <i>Crystal Research and Technology</i> , 1990 , 25, 1299-1302	1.3	5